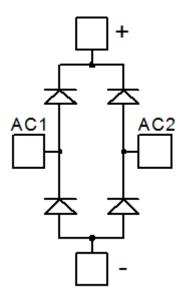
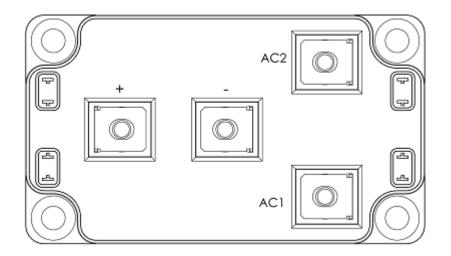


# MSCDC100H70AG SiC Diode Full Bridge Power Module

# **1 Product Overview**

This section shows the product overview of the MSCDC100H70AG device.





All ratings at  $T_j = 25$  °C, unless otherwise specified.

**Caution**: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.



# 1.1 Features

The following are key features of the MSCDC100H70AG device:

- Silicon carbide (SiC) Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature-independent switching behavior
  - Positive temperature coefficient on VF
- High blocking voltage
- Low stray inductance
- M5 power connectors
- Aluminum nitride (AIN) substrate for improved thermal performance

## 1.2 Benefits

The following are benefits of the MSCDC100H70AG device:

- Outstanding performance at high-frequency operation
- Low losses
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS compliant

# **1.3** Applications

The MSCDC100H70AG device is designed for the following applications:

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers



# 2 Electrical Specifications

This section shows the electrical specifications of the MSCDC100H70AG device.

# 2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode of the MSCDC100H70AG device.

#### Table 1 • Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
Vrrm	Repetitive peak reverse voltage		700	V
lf	DC forward current	Tc = 70 °C	100	А

The following table shows the thermal and package characteristics of the MSCDC100H70AG device.

#### Table 2 • Thermal and Package Characteristics

Symbol	Characteristic			Min	Max	Unit
VISOL	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz			4000		V
Ti	Operating junction temperature range			-40	175	°C
Τιορ	Recommended junction temperature under switching conditions			-40	T <sub>Jmax</sub> -25	-
Tstg	Storage temperature range			-40	125	-
Tc	Operating case temperature			-40	125	_
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	_
Wt	Package weight				300	g

# 2.2 Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSCDC100H70AG device.

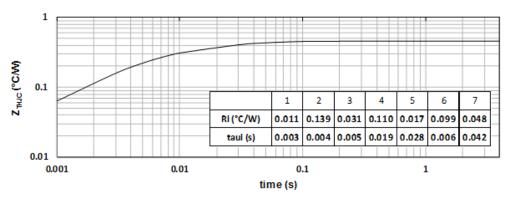
Symbol	Characteristic	Test Conditions	;	Min	Тур	Max	Unit
VF	Diode forward voltage	IF = 100 A	T <sub>j</sub> = 25 °C		1.5	1.8	V
			T <sub>j</sub> = 175 °C		1.9		-
Irm	Reverse leakage current	V <sub>R</sub> = 700 V	T <sub>j</sub> = 25 °C		30	400	μΑ
			T <sub>j</sub> = 175 °C		500		-
Qc	Total capacitive charge	V <sub>R</sub> = 400 V			266		nC
С	Total capacitance	f = 1 MHz, V <sub>R</sub> = 200 V			496		pF
		f = 1 MHz, V <sub>R</sub> =	400 V		432		_
RthJC	Junction-to-case thermal resist	ance				0.456	°C/W

### Table 3 • Electrical Characteristics



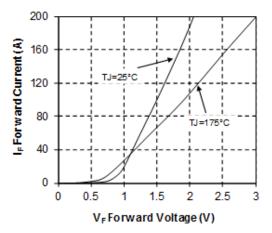
# 2.3

**Typical Performance Curves** This section shows the typical performance curves of the MSCDC100H70AG device.

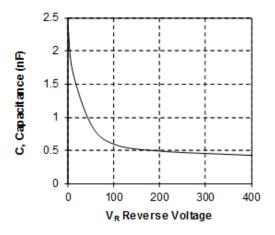


### Figure 1 • Maximum Transient Thermal Impedance











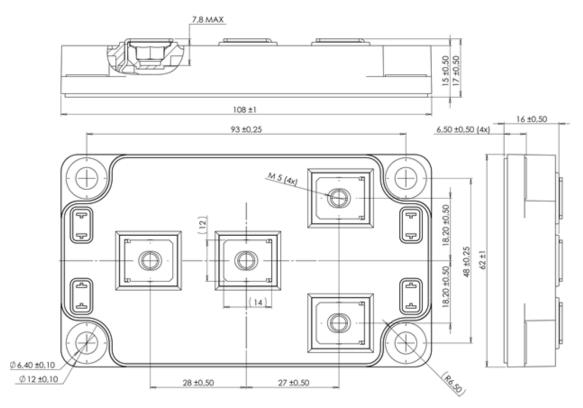
#### **Package Specification** 3

This section shows the package specifications for the MSCDC100H70AG device.

# 3.1

**Package Outline Drawing** The package outline of the MSCDC100H70AG device is illustrated in this section. The dimensions in the following figure are in millimeters.

#### Figure 4 • Package Outline Drawing







а 🔨 Міскоснір company

#### Microsemi Headquarters One Enterprise, Aliso Viejo, CA 92556 USA Within the USA: +1 (800) 713-4113 Outside the USA: +1 (949) 380-6100 Sales: +1 (949) 380-6136 Fax: +1 (949) 215-4996 Email: sales.support@microsemi.com

© 2019 Microsemi. All rights reserved. Microsemi and the Microsemi logo are trademarks of Microsemi Corporation. All other trademarks and service marks are the property of their respective owners. Microsemi makes no warranty, representation, or guarantee regarding the information contained herein or the suitability of its products and services for any particular purpose, nor does Microsemi assume any liability whatsoever arising out of the application or use of any product or circuit. The products sold by Microsemi have been subject to limited testing and should not be used in conjunction with mision-critical equipment or applications. Any performance specifications are believed to be reliable but are not verified, and Buyer must conduct and complete all performance and other testing of the products, alone and together with, or installed in, any end-products. Buyer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the Buyer's responsibility to independently determine suitability of any products and to test and verify the same. The information provided by Microsemi hereunder is provided "as is, where is" and with all faults, and the entire risk associated with such information is entirely with the Buyer. Microsemi does not grant, explicitly or implicitly, to any part any patent rights, licenses, or any other IP rights, whether with regard to such information itself or anything described by such information. Information provided in this document is proprietary to Microsemi, and Microsemi reserves the right to make any changes to the information in this document or to any products and services at any time without notice.

Microsemi, a wholly owned subsidiary of Microchip Technology Inc. (Nasdaq: MCHP), offers a comprehensive portfolio of semiconductor and system solutions for aerospace & defense, communications, data center and industrial markets. Products include high-performance and radiation-hardened analog mixed-signal integrated circuits, FPGAS, SoCs and ASICs; power management products; timing and synchronization devices and precise time solutions; security technologies and scalable anti-tamper products; thermet solutions; discrete components; enterprise storage and communication solutions; security technologies and scalable anti-tamper products; thermet solutions; Power-over-Ethernet ICs and midspans; as well as custom design capabilities and services. Microsemi is headquartered in Aliso Viejo, California, and has approximately 4,800 employees globally. Learn more at www microsemi.com.

MSCC-0344-DS-01025-1.0-0619 | June 2019 | Final

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Microchip: MSCDC100H70AG